

2SK3447

Silicon N Channel Power MOS FET Power Switching

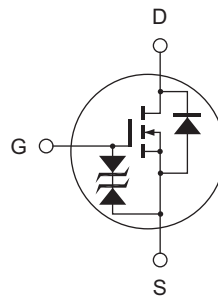
REJ03G1101-0700
(Previous: ADE-208-1567E)
Rev.7.00
Sep 07, 2005

Features

- Capable of 4 V gate drive
- Low drive current
- Low on-resistance
 $R_{DS(on)} = 1.5 \Omega$ typ. (at $V_{GS} = 10 V$)

Outline

RENESAS Package code: PRSS0003DC-A
(Package name: TO-92MOD)



1. Source
2. Drain
3. Gate

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Drain to source voltage	V _{DSS}	150	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	1	A
Drain peak current	I _{D (pulse)} ^{Note 1}	4	A
Body-drain diode reverse drain current	I _{DR}	1	A
Channel dissipation	P _{ch} ^{Note 2}	0.9	W
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1%
 2. Value at Ta = 25°C

Electrical Characteristics

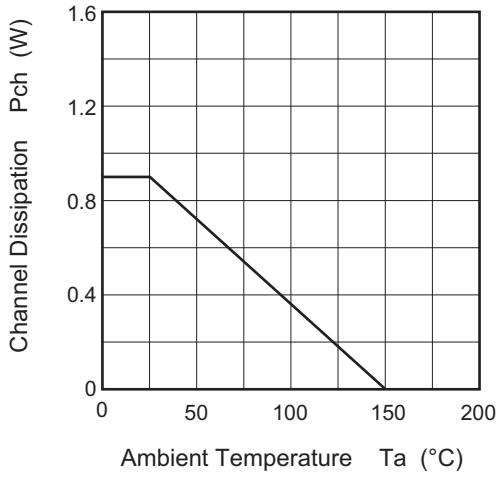
(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	V _{(BR) DSS}	150	—	—	V	I _D = 10 mA, V _{GS} = 0
Gate to source breakdown voltage	V _{(BR) GSS}	±20	—	—	V	I _G = ±100 μA, V _{DS} = 0
Gate to source leak current	I _{GSS}	—	—	±10	μA	V _{GS} = ±16 V, V _{DS} = 0
Zero gate voltage drain current	I _{DSS}	—	—	1	μA	V _{DS} = 150 V, V _{GS} = 0
Gate to source cutoff voltage	V _{GS (off)}	1.0	—	2.5	V	V _{DS} = 10 V, I _D = 1 mA
Static drain to source on state resistance	R _{DS (on)}	—	1.5	1.95	Ω	I _D = 0.5 A, V _{GS} = 10 V ^{Note 3}
	R _{DS (on)}	—	1.9	2.5	Ω	I _D = 0.5 A, V _{GS} = 4 V ^{Note 3}
Forward transfer admittance	y _{fs}	0.5	0.9	—	S	I _D = 0.5 A, V _{DS} = 10 V ^{Note 3}
Input capacitance	C _{iss}	—	85	—	pF	V _{DS} = 10 V V _{GS} = 0 f = 1 MHz
Output capacitance	C _{oss}	—	36	—	pF	
Reverse transfer capacitance	C _{rss}	—	18	—	pF	
Total gate charge	Q _g	—	4.5	—	nC	V _{DD} = 100 V
Gate to source charge	Q _{gs}	—	0.8	—	nC	V _{GS} = 10 V
Gate to drain charge	Q _{gd}	—	1.6	—	nC	I _D = 1 A
Turn-on delay time	t _{d (on)}	—	7	—	ns	V _{GS} = 10 V I _D = 0.5 A R _L = 60 Ω
Rise time	t _r	—	6	—	ns	
Turn-off delay time	t _{d (off)}	—	21	—	ns	
Fall time	t _f	—	10	—	ns	
Body-drain diode forward voltage	V _{DF}	—	1.0	1.5	V	I _F = 1 A, V _{GS} = 0 ^{Note 3}
Body-drain diode reverse recovery time	t _{rr}	—	60	—	ns	I _F = 1 A, V _{GS} = 0 di _F /dt = 100 A/μs

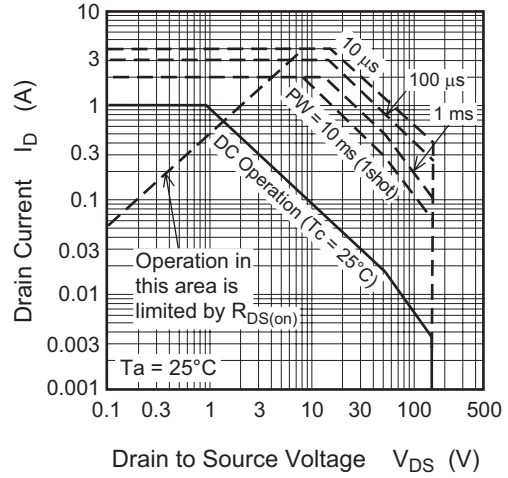
Note: 3. Pulse test

Main Characteristics

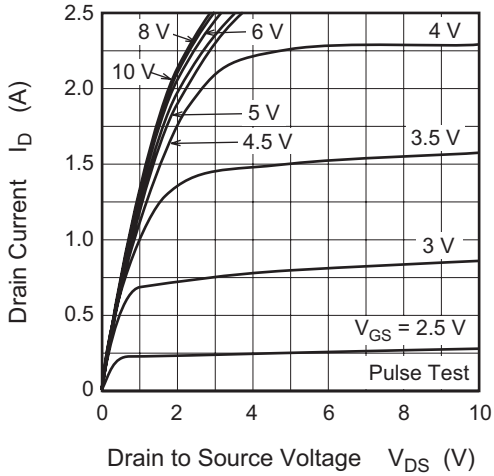
Power vs. Temperature Derating



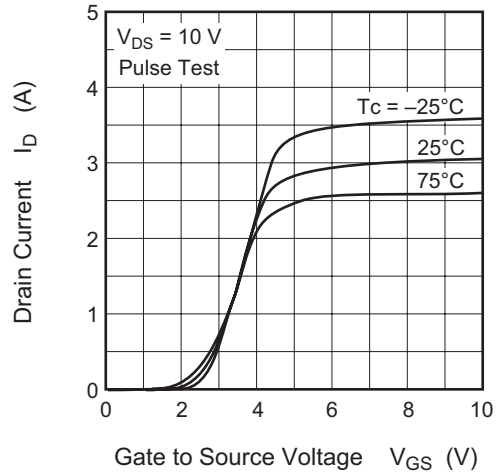
Maximum Safe Operation Area



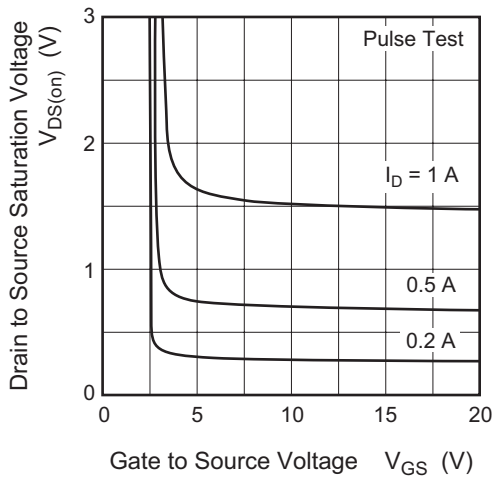
Typical Output Characteristics



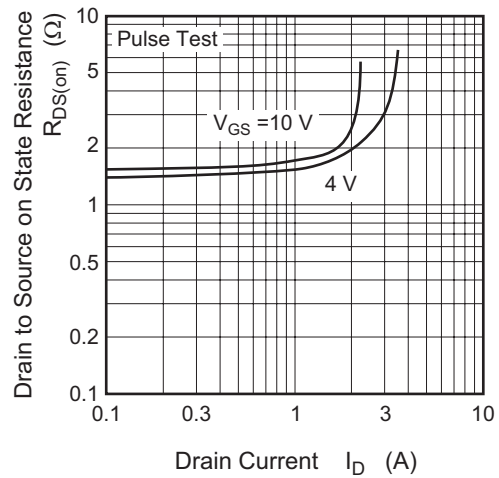
Typical Transfer Characteristics



Drain to Source Saturation Voltage vs. Gate to Source Voltage

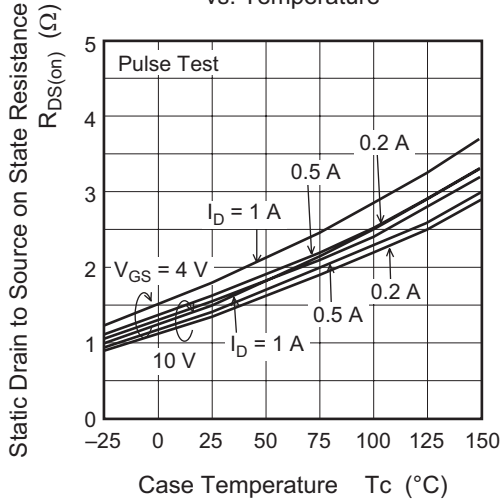


Static Drain to Source on State Resistance vs. Drain Current

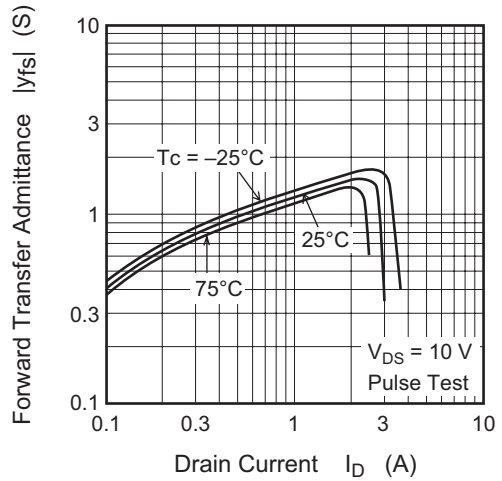


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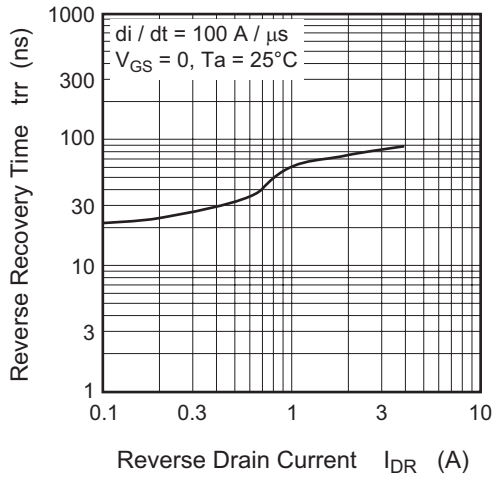
Static Drain to Source Resistance vs. Temperature



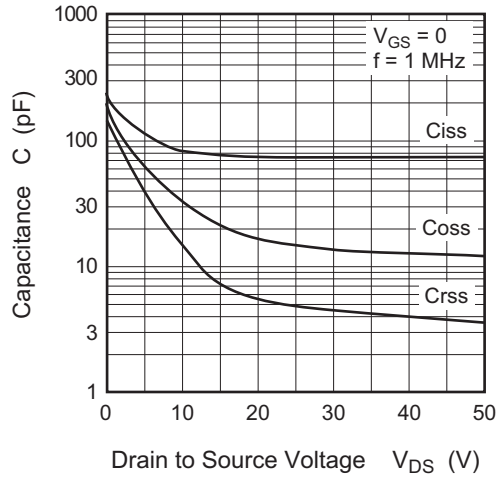
Forward Transfer Admittance vs. Drain Current



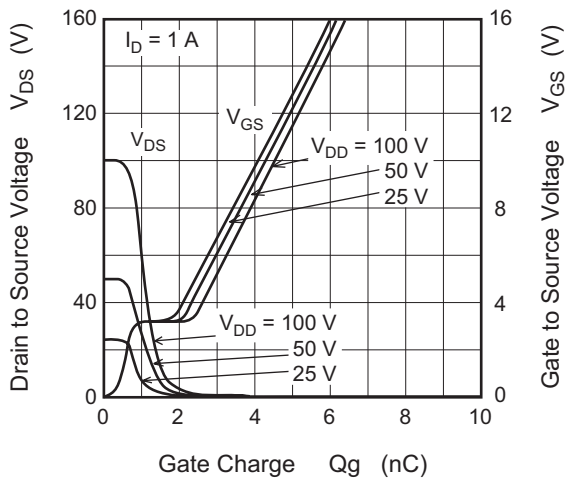
Body-Drain Diode Reverse Recovery Time



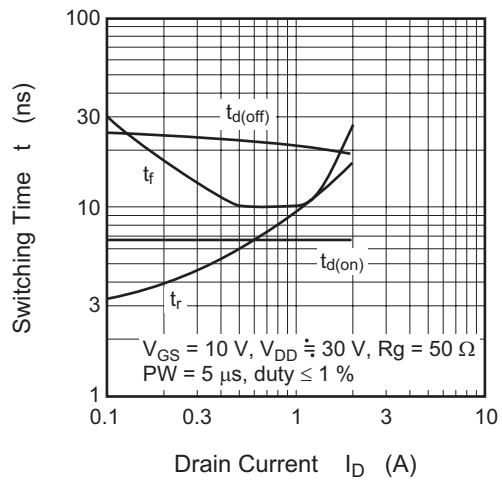
Typical Capacitance vs. Drain to Source Voltage



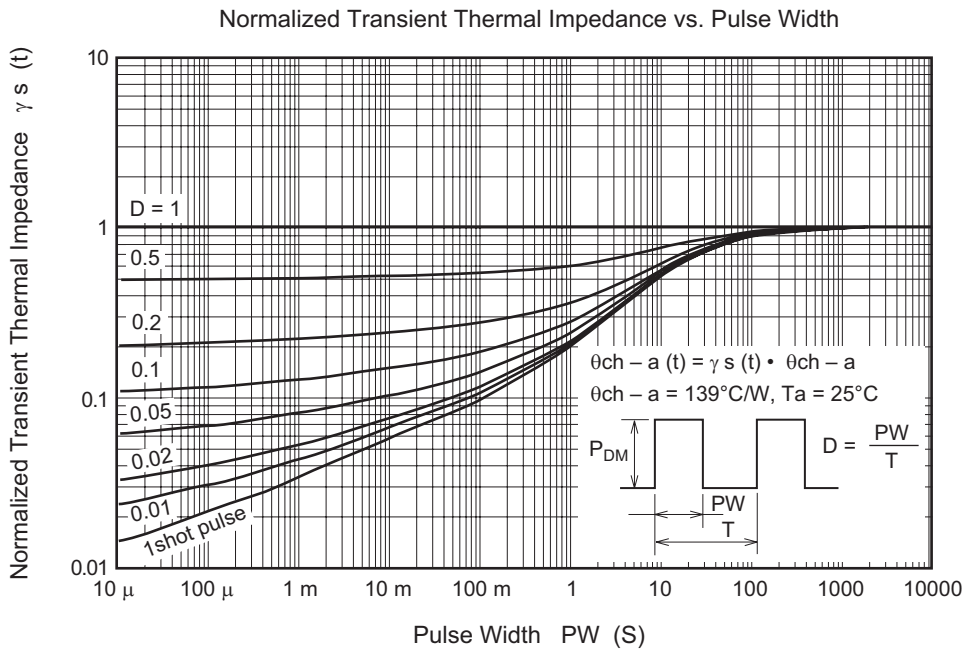
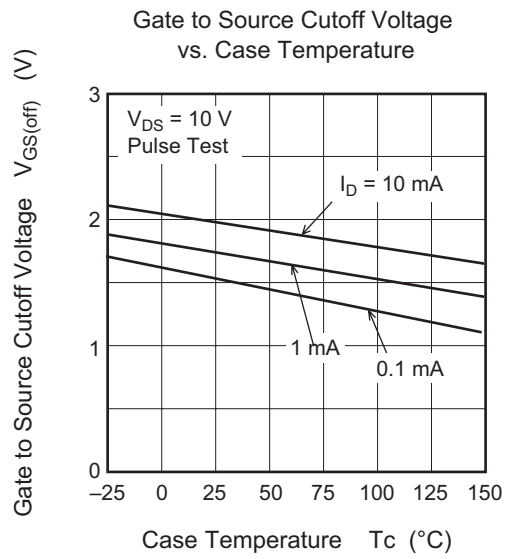
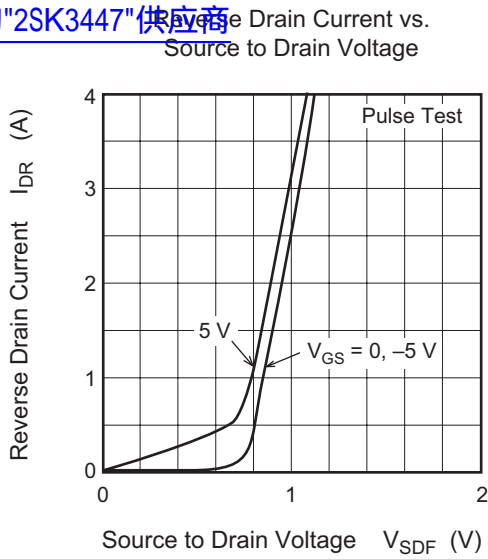
Dynamic Input Characteristics



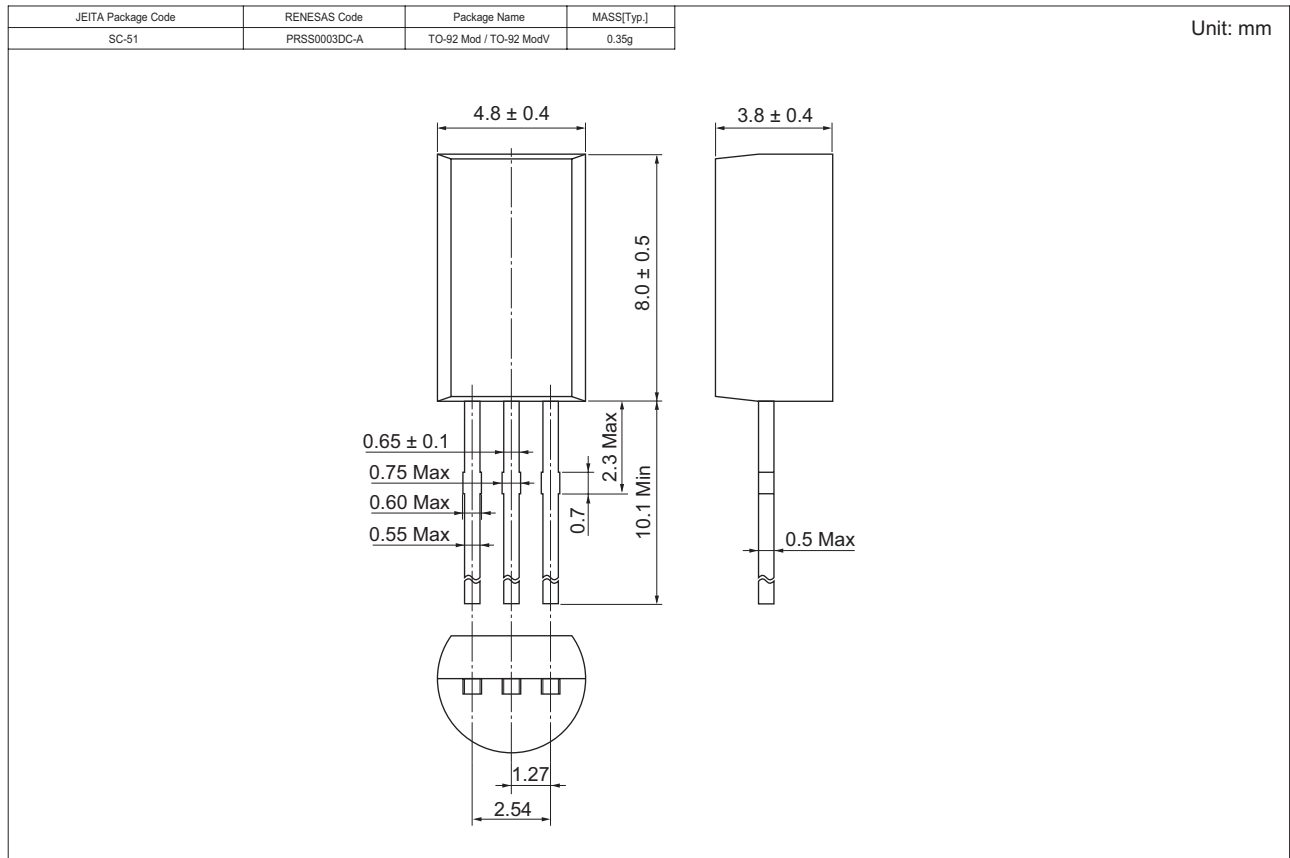
Switching Characteristics



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Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SK3447TZ-E	2500 pcs	Hold box, Radial taping

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Renesas Technology Europe Limited

Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
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Renesas Technology Hong Kong Ltd.

7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong
Tel: <852> 2265-6688, Fax: <852> 2730-6071

Renesas Technology Taiwan Co., Ltd.

10th Floor, No.99, Fushing North Road, Taipei, Taiwan
Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology (Shanghai) Co., Ltd.

Unit2607 Ruijing Building, No.205 Maoming Road (S), Shanghai 200020, China
Tel: <86> (21) 6472-1001, Fax: <86> (21) 6415-2952

Renesas Technology Singapore Pte. Ltd.

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Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd.

Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea
Tel: <82> 2-796-3115, Fax: <82> 2-796-2145

Renesas Technology Malaysia Sdn. Bhd.

Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: <603> 7955-9390, Fax: <603> 7955-9510